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(54) STACKED TRANSISTORS HAVING SELF ALIGNED BACKSIDE CONTACT WITH BACKSIDE REPLACEMENT METAL GATE

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(57)**ABSTRACT**

A semiconductor structure including stacked transistor structures each including a top device stacked directly above a bottom device, and a placeholder dielectric and a backside gate contact within a dielectric capping layer beneath the stacked transistor structures, where the placeholder dielectric is directly below a first bottom source drain region, and the backside gate contact is directly below a second bottom source drain region.

